

	Type	L #	Hits	Search Text	DBs
1	IS&R	L1	1010	(327/427).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	IS&R	L2	678	(327/434).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	32701	transistor.clm.	US-PGPUB
4	BRS	L4	1298	3 and (body substrate well bulk backgate back adj gate) near2 drain.clm.	US-PGPUB
5	BRS	L5	337	4 and (storage capacitor).clm.	US-PGPUB
6	BRS	L6	105	5 and (current adj direct\$3 anode cathode diode rectif\$4 direct\$3).clm.	US-PGPUB
7	BRS	L7	101	6 and (gate control adj terminal).clm.	US-PGPUB